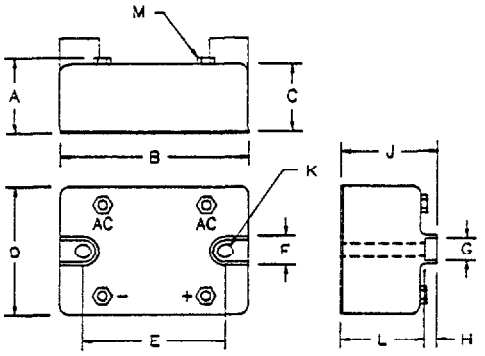
Single Phase Bridge Modules
EH60, EH75



Dim.	Inches		Millimeter		
	Minimum	Maximum	Minimum	Maximum	Notes
A	—	1.10	—	27.94	
B	2.25	2.40	57.15	60.96	
C	.930	.950	23.62	24.13	
D	1.740	1.760	44.19	44.70	
E	1.883	1.887	47.82	47.92	
F	.495	.505	12.57	12.83	
G	.325	.335	8.25	8.50	
H	.215	.225	5.46	5.71	
J	1.270	1.300	32.25	33.02	
K	.198	.208	5.02	5.28	Dia.
L	1.055	1.075	26.79	27.30	
M	#10–32 Tapped Holes				

Microsemi Catalog Number		Repetitive Peak Reverse Voltage
EH6002B*	EH7502B*	200
EH6004B*	EH7504B*	400
EH6006B*	EH7506B*	600
EH6008B*	EH7508B*	800
EH6010B*	EH7510B*	1000
EH6012B*	EH7512B*	1200

*Add S for Transient Suppressor across output

- Integral Transient Supression Available
- High Terminal–to–base Isolation of 2500VAC RMS
- Available to 1200V
- Mounting Bolts Isolated From Power Terminals

E

Electrical Characteristics

		EH60	EH75	
Maximum DC output current, single phase	I_O	60A	75A	Sine wave, 180° conduction
Maximum case temperature	T_C	104°C	105°C	
Maximum surge current per diode	I_{FSM}	1050A	1500A	8.3ms, half sine, T_J = 175°C
Max. I^2t for fusing	I^2t	4600A^2S	9300A^2S	
Max. peak forward voltage per diode	V_{FM}	1.2V	1.1V	@ I_O; T_J = 25°C
Max. peak reverse voltage per diode	I_{RM}	4mA		V_{RRM}, T_J = 150°C
Minimum isolation voltage	V_{ISOL}	2500V_{RMS}		any terminal–to–base

Thermal and Mechanical Characteristics

Storage temp range	T_{STG}	–40°C to 175°C
Operating junction temp range	T_J	–40°C to 175°C
Max thermal resistance per diode	EH60 $R_{\theta JC}$	1.0°C/W Junction to case
	EH75 $R_{\theta JC}$	0.85°C/W Junction to case
Max mounting torque		30 lb–in
Typical thermal resistance	$R_{\theta CS}$	0.07°C/W Case to sink
Typical Weight		5.8 ounces (165 grams)

PH: 303-469-2161
FAX: 303-400-3775

Microsemi Corp.
Colorado

EH60, EH75

Figure 1
Typical Forward Characteristics – Per Diode

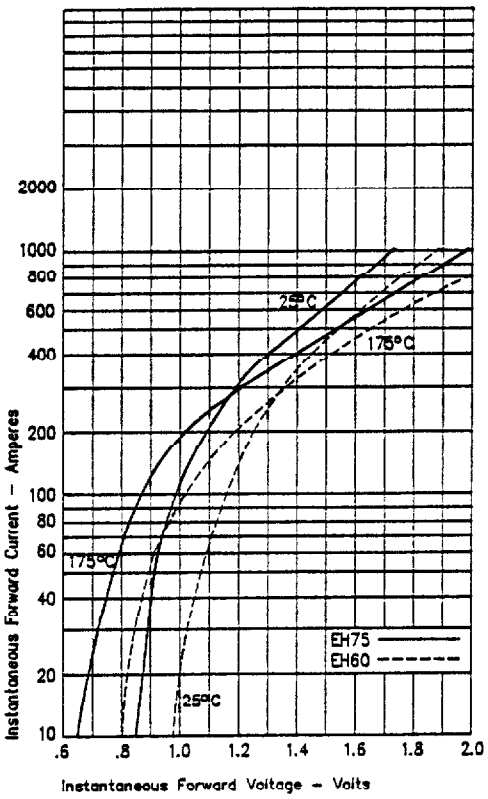


Figure 2
Forward Current Derating – Per Diode

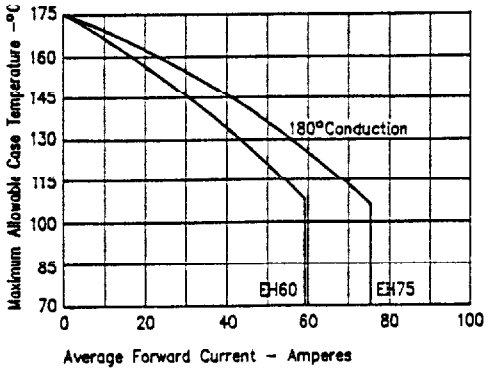
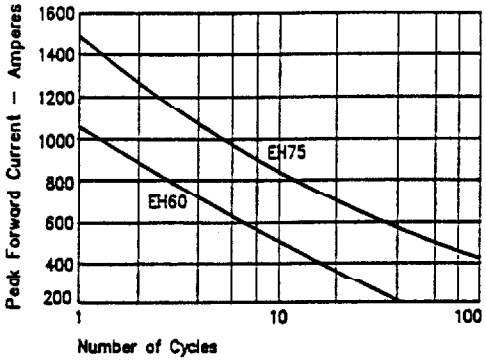



Figure 3
Maximum Nonrepetitive Surge Current – Per Diode